

1. Scope :

This specification applies to PN silicon photodiode chips,
Device NO. PD-0240.

2. Structure :

- 2-1. Planar type : PN Diode.
- 2-2. Electrodes :
Top side (Anode) : Aluminum alloy .
Back side (Cathode) : Gold alloy .

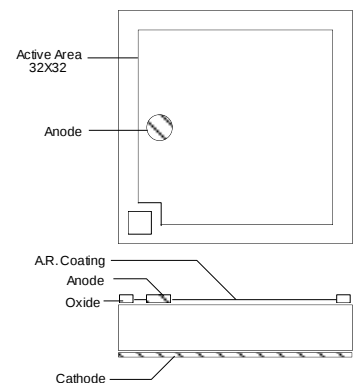
3. Size :

- 3-1. Chip size : 40 mils × 40 mils (1.016 mm × 1.016 mm).
- 3-2. Chip thickness : 8.6 ± 1.2 mils (0.220 ± 0.030 mm).
- 3-3. Active area : 32 mils × 32 mils (0.813 mm × 0.813 mm).
- 3-4. Bonding pad (Anode) : 5.4 mils (0.137 mm) Diameter.
- 3-5. Pattern drawing: Refer to the attached drawing.

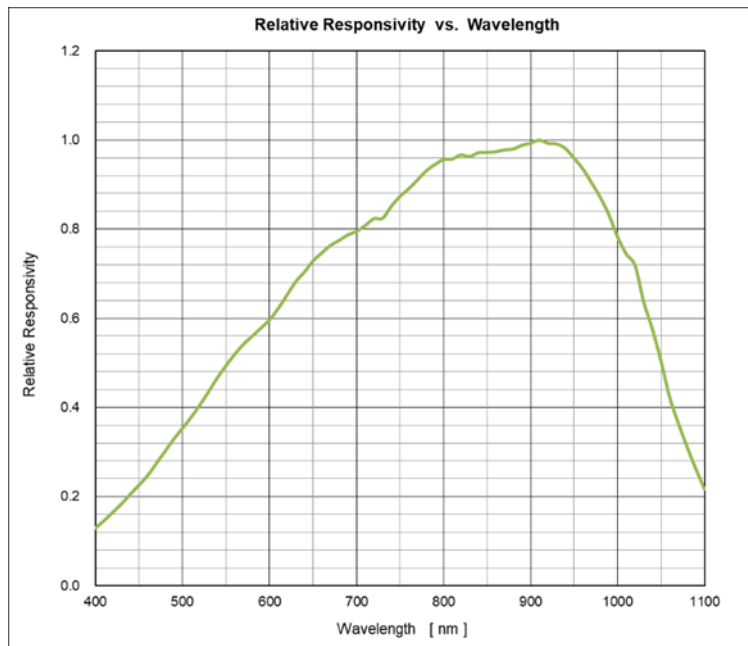
4. Electro-optical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
*Reverse dark Current	I_D	$V_R=10V$ $E_e=0mW/cm^2$			10	nA
*Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu A$ $E_e=0mW/cm^2$	33			V
Open circuit Voltage	V_{oc}	$T=2856K$ $E_e=5mW/cm^2$		410		mV
Short circuit Current	I_{sc}	$T=2856K$ $E_e=5mW/cm^2$		7		μA
Reverse light Current	I_L	$V_R=5V$ $T=2856K$ $E_e=5mW/cm^2$		7		μA
Total Capacitance	C_T	$V_R=5V$ $E_e=0mW/cm^2$ $f=1MHz$		21		pF

*Based on 100% probing



5. Relative spectral responsivity



*: Bare chip measured with integrating sphere, for reference only.